

Jose Alvarez

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8884623/publications.pdf>

Version: 2024-02-01

58
papers

1,031
citations

471509

17
h-index

434195

31
g-index

58
all docs

58
docs citations

58
times ranked

1218
citing authors

#	ARTICLE	IF	CITATIONS
1	Single Schottky-barrier photodiode with interdigitated-finger geometry: Application to diamond. Applied Physics Letters, 2007, 90, 123507.	3.3	96
2	Thermally stable visible-blind diamond photodiode using tungsten carbide Schottky contact. Applied Physics Letters, 2005, 87, 022105.	3.3	94
3	Persistent positive and transient absolute negative photoconductivity observed in diamond photodetectors. Physical Review B, 2008, 78, .	3.2	75
4	Thermally stable solar-blind diamond UV photodetector. Diamond and Related Materials, 2006, 15, 1962-1966.	3.9	69
5	Comprehensive Investigation of Single Crystal Diamond Deep-Ultraviolet Detectors. Japanese Journal of Applied Physics, 2012, 51, 090115.	1.5	60
6	Photovoltaic Schottky ultraviolet detectors fabricated on boron-doped homoepitaxial diamond layer. Applied Physics Letters, 2006, 88, 033504.	3.3	43
7	Comprehensive Investigation of Single Crystal Diamond Deep-Ultraviolet Detectors. Japanese Journal of Applied Physics, 2012, 51, 090115.	1.5	43
8	Thermal Stability of Diamond Photodiodes Using Tungsten Carbide as Schottky Contact. Japanese Journal of Applied Physics, 2005, 44, 7832-7838.	1.5	38
9	Diamond UV detectors for future solar physics missions. Diamond and Related Materials, 2001, 10, 673-680.	3.9	37
10	Conductive-probe atomic force microscopy characterization of silicon nanowire. Nanoscale Research Letters, 2011, 6, 110.	5.7	37
11	Observation by conductive-probe atomic force microscopy of strongly inverted surface layers at the hydrogenated amorphous silicon/crystalline silicon heterojunctions. Applied Physics Letters, 2010, 97, .	3.3	29
12	Large deep-ultraviolet photocurrent in metal-semiconductor-metal structures fabricated on as-grown boron-doped diamond. Applied Physics Letters, 2005, 87, 113507.	3.3	28
13	Characterization of graphene oxide reduced through chemical and biological processes. Journal of Physics: Conference Series, 2013, 433, 012001.	0.4	22
14	Revisiting the theory and usage of junction capacitance: Application to high efficiency amorphous/crystalline silicon heterojunction solar cells. Solar Energy Materials and Solar Cells, 2015, 135, 8-16.	6.2	21
15	Recent progresses of the BOLD investigation towards UV detectors for the ESA Solar Orbiter. Diamond and Related Materials, 2002, 11, 427-432.	3.9	19
16	Characterization of silicon heterojunctions for solar cells. Nanoscale Research Letters, 2011, 6, 152.	5.7	19
17	Understanding inversion layers and band discontinuities in hydrogenated amorphous silicon/crystalline silicon heterojunctions from the temperature dependence of the capacitance. Applied Physics Letters, 2013, 103, .	3.3	17
18	Cross-Sectional Investigations on Epitaxial Silicon Solar Cells by Kelvin and Conducting Probe Atomic Force Microscopy: Effect of Illumination. Nanoscale Research Letters, 2016, 11, 55.	5.7	17

#	ARTICLE	IF	CITATIONS
19	Study of traps in P3HT:PCBM based organic solar cells using fractional thermally stimulated current (FTSC) technique. Journal of Non-Crystalline Solids, 2012, 358, 2537-2540.	3.1	16
20	Crystallographic and electrical characterization of tungsten carbide thin films for Schottky contact of diamond photodiode. Journal of Vacuum Science & Technology B, 2006, 24, 185.	1.3	14
21	Schottky-barrier photodiode using p-diamond epilayer grown on p+-diamond substrates. Diamond and Related Materials, 2009, 18, 296-298.	3.9	14
22	Diamond dosimeter for small beam stereotactic radiotherapy. Diamond and Related Materials, 2013, 33, 63-70.	3.9	14
23	Electrical characterization of Schottky diodes based on boron doped homoepitaxial diamond films by conducting probe atomic force microscopy. Superlattices and Microstructures, 2006, 40, 343-349.	3.1	13
24	Submicron metal-semiconductor-metal diamond photodiodes toward improving the responsivity. Applied Physics Letters, 2007, 91, 163510.	3.3	13
25	Dislocation and antiphase domain free microscale GaAs crystals grown on SiO ₂ from (001) Si nano-areas. Applied Physics Letters, 2013, 102, 191915.	3.3	13
26	Schottky photodiode using submicron thick diamond epilayer for flame sensing. Nano-Micro Letters, 2009, 1, 30-33.	27.0	12
27	Amorphous silicon diamond based heterojunctions with high rectification ratio. Journal of Non-Crystalline Solids, 2012, 358, 2110-2113.	3.1	12
28	New UV detectors for solar observations. , 2003, 4853, 419.		11
29	Development of imaging arrays for solar UV observations based on wide band gap materials. , 2004, , .		11
30	Study of deep defects in polycrystalline CVD diamond from thermally stimulated current and below-gap photocurrent experiments. Diamond and Related Materials, 2003, 12, 546-549.	3.9	10
31	Local photoconductivity on diamond metal-semiconductor-metal photodetectors measured by conducting probe atomic force microscopy. Diamond and Related Materials, 2007, 16, 1074-1077.	3.9	10
32	Giant and reversible enhancement of the electrical resistance of GaAs _{1-x} N _x by hydrogen irradiation. Physical Review B, 2011, 84, .	3.2	10
33	On the metastability of the surface conductivity in hydrogen-terminated polycrystalline CVD diamond. Diamond and Related Materials, 2004, 13, 751-754.	3.9	9
34	Tungsten carbide Schottky contact to diamond toward thermally stable photodiode. Diamond and Related Materials, 2005, 14, 2003-2006.	3.9	9
35	Vertical-type Schottky-barrier photodiode using p-diamond epilayer grown on heavily boron-doped p+-diamond substrate. Diamond and Related Materials, 2008, 17, 1916-1921.	3.9	7
36	High current density GaAs/Si rectifying heterojunction by defect free Epitaxial Lateral overgrowth on Tunnel Oxide from nano-seed. Scientific Reports, 2016, 6, 25328.	3.3	7

#	ARTICLE	IF	CITATIONS
37	Relaxation in undoped polycrystalline CVD diamond films under red illumination. <i>Diamond and Related Materials</i> , 2002, 11, 635-639.	3.9	6
38	Very high UV-visible selectivity in polycrystalline CVD diamond films. <i>Diamond and Related Materials</i> , 2004, 13, 881-885.	3.9	6
39	Development of Thermally Stable, Solar-Blind Deep-Ultraviolet Diamond Photosensor. <i>Materials Transactions</i> , 2005, 46, 1965-1968.	1.2	6
40	Ultraviolet Detectors Based on Ultravioletâ€“Ozone Modified Hydrogenated Diamond Surfaces. <i>Applied Physics Express</i> , 0, 2, 065501.	2.4	6
41	Growth of high quality micrometer scale GaAs/Si crystals from (001) Si nano-areas in SiO ₂ . <i>Journal of Crystal Growth</i> , 2014, 401, 554-558.	1.5	6
42	Local electrical characterization of Schottky diodes on H-terminated diamond surfaces by conducting probe atomic force microscopy. <i>Diamond and Related Materials</i> , 2006, 15, 618-621.	3.9	5
43	Nanowire solar cells using hydrogenated amorphous silicon: A modeling study. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 1026-1030.	1.8	5
44	Electronic properties of CVD polycrystalline diamond films. <i>Diamond and Related Materials</i> , 2001, 10, 588-592.	3.9	4
45	Tin dioxide nanoparticles as catalyst precursors for plasma-assisted vaporâ€“liquidâ€“solid growth of silicon nanowires with well-controlled density. <i>Nanotechnology</i> , 2018, 29, 435301.	2.6	3
46	Recent Progress in Understanding the Properties of the Amorphous Silicon/Crystalline Silicon Interface. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800877.	1.8	3
47	InP-based nano solar cells. , 2014, , .		2
48	Temperature and bias dependence of hydrogenated amorphous silicon â€“ crystalline silicon heterojunction capacitance: the link to band bending and band offsets. <i>Canadian Journal of Physics</i> , 2014, 92, 690-695.	1.1	2
49	On the equilibrium electrostatic potential and lightâ€“induced charge redistribution in halide perovskite structures. <i>Progress in Photovoltaics: Research and Applications</i> , 2022, 30, 994-1002.	8.1	2
50	Space charge capacitance spectroscopy in amorphous silicon Schottky diodes: Theory, modeling, and experiments. <i>Journal of Non-Crystalline Solids</i> , 2012, 358, 2007-2010.	3.1	1
51	Modelling on c-Si/a-Si:H wire solar cells: some key parameters to optimize the photovoltaic performance. <i>EPJ Photovoltaics</i> , 2012, 3, 30102.	1.6	1
52	Explicit analytical modeling of the low frequency a-Si:H/c-Si heterojunction capacitance: Analysis and application to silicon heterojunction solar cells. <i>Journal of Applied Physics</i> , 2015, 118, 114507.	2.5	1
53	GaAs microcrystals selectively grown on silicon: Intrinsic carbon doping during chemical beam epitaxy with trimethylgallium. <i>Journal of Applied Physics</i> , 2017, 121, 035704.	2.5	1
54	Optoelectrical modeling of solar cells based on c-Si/a-Si:H nanowire array: focus on the electrical transport in between the nanowires. <i>Nanotechnology</i> , 2018, 29, 255401.	2.6	1

#	ARTICLE	IF	CITATIONS
55	Observation of photovoltaic effect within locally doped silicon nanojunctions using conductive probe AFM. Nano Energy, 2020, 76, 105072.	16.0	1
56	Modeling of capacitance spectroscopy of (p) a-Si:H/(n) c-Si interfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1481-1483.	0.8	0
57	Wide-Bandgap Semiconductors: Nanostructures, Defects, and Applications. Journal of Nanomaterials, 2015, 2015, 1-2.	2.7	0
58	Analytical model of the modulated photoluminescence in semiconductor materials. Journal Physics D: Applied Physics, 2022, 55, 105103.	2.8	0